

LISTING OF CLAIMS

1. (Currently amended) An alkaline composition having a pH of 9 or greater for stripping or cleaning integrated circuit substrates, comprising:
 - (a) one or more bases; and
 - (b) 0.05% to 10% by weight of one or more metal halide compounds of the formula:
$$W_zMX_y$$
where M is a metal selected from the group consisting of Si, Ge, Sn, Pt, P, B, Au, Ir, Os, Cr, Ti, Zr, Rh, Ru, and Sb; X is a halide selected from the group consisting of F, Cl, Br and I; W is selected from the group consisting of H, an alkali or alkaline earth metal, and a metal ion-free hydroxide base moiety; y is a numeral of from 4 to 6 depending on the metal halide; and z is a numeral of from 1, 2 or 3.
2. (Previously presented) A composition according to claim 1 wherein the composition is an aqueous, alkaline composition, the base component (a) is a metal ion-free bases and the base is present in the composition in an amount sufficient to produce a pH of the composition of from about 10 to about 13, ~~and wherein the one or more metal halide compounds is present in the composition an amount of from about 0.5% to about 10% by weight of the composition.~~
3. (Cancelled)
4. (Cancelled)
5. (Previously presented) The composition of claim 1 wherein the base component (a) is selected from the group consisting of ammonium hydroxide, quaternary ammonium hydroxides and diamines.

6. (Original) The composition of claim 5 wherein the base component (a) is a tetraalkyl ammonium hydroxide containing alkyl groups of from 1 to 4 carbon atoms.
7. (Previously presented) The composition of claim 2 wherein M is selected from the group consisting of Si, Ge, Zr and Sb.
8. (Cancelled)
9. (Cancelled)
10. (Original) The composition of claim 7 wherein the metal halide is selected from the group consisting of H_2SiF_6 , H_2GeF_6 , $((CH_3)_4N)_2GeF_6$, $((CH_3)_4N)_2SiF_6$, $(NH_4)_2SiF_6$ and $(NH_4)_2GeF_6$.
11. (Cancelled)
12. (Cancelled)
13. (Original) The composition of claim 10 wherein the metal halide is H_2SiF_6 .
14. (Cancelled)
15. (Cancelled)
16. (Cancelled)

17. (Original) The composition of claim 2 additionally comprising one or more additional components selected from the group consisting of organic solvents and co-solvents, metal chelating or complexing agents, silicates, fluorides, additional metal corrosion inhibitors, surfactants, titanium residue removal enhancing agents, oxidizing agents and bath stabilizing agents.
18. (Cancelled)
19. (Previously presented) A composition of claim 2 comprising tetramethylammonium hydroxide, trans-(1,2-cyclohexylenedinitrilo)tetraacetic acid, hydrogen peroxide, water, and a metal halide compound selected from the group consisting of dihydrogen hexafluorosilicate, dihydrogenhexafluorogermanate, and ammonium hexafluorogermanate.
20. (Original) A composition according to claim 19 having a pH of about 11.5.
21. (Cancelled)
22. (Cancelled)
23. (Cancelled)
24. (Cancelled)
25. (Currently amended) A method for cleaning semiconductor wafer substrates, comprising:
contacting a semiconductor wafer substrate having a substrate surface for a time and at a temperature sufficient to clean unwanted contaminants and residues from

said substrate surface with a an alkaline composition having a pH of 9 or greater and comprising:

(a) one or more bases; and

(b) 0.5% to 10% by weight of the composition of one or more metal halide compounds of the formula:



where M is a metal selected from the group consisting of Si, Ge, Sn, Pt, P, B, Au, Ir, Os, Cr, Ti, Zr, Rh, Ru, and Sb; X is a halide selected from the group consisting of F, Cl, Br and I; W is selected from the group consisting of H, an alkali or alkaline earth metal, and a metal ion-free hydroxide base moiety; y is a numeral of from 4 to 6 depending on the metal halide; and z is a numeral of from 1, 2 or 3.

26. (Currently amended) A method according to claim 25 wherein the composition is an aqueous, alkaline composition, the base component (a) is a metal ion-free bases and the base is present in the composition in an amount sufficient to produce a pH of the composition of from about 10 to about 13, ~~and wherein the one or more metal halide compounds is present in the composition an amount of from about 0.5% to about 10% by weight of the composition.~~

27. (Cancelled)

28. (Cancelled)

29. (Previously presented) The method of claim 25 wherein the base component (a) is selected from the group consisting of ammonium hydroxide, quaternary ammonium hydroxides and diamines.

30. (Previously presented) The method of claim 29 wherein the base component (a) is a tetraalkyl ammonium hydroxide containing alkyl groups of from 1 to 4 carbon atoms.
31. (Currently amended) The method of claim 26 wherein M is selected from the group consisting of Si, Ge, Zr and Sb.
32. (Cancelled)
33. (Cancelled)
34. (Previously presented) The method of claim 31 wherein the metal halide is selected from the group consisting of H_2SiF_6 , H_2GeF_6 , $((CH_3)_4N)_2GeF_6$, $((CH_3)_4N)_2SiF_6$, $(NH_4)_2SiF_6$ and $(NH_4)_2GeF_6$.
35. (Cancelled)
36. (Cancelled)
37. (Previously presented) The method of claim 34 wherein the metal halide is H_2SiF_6 .
38. (Cancelled)
39. (Cancelled)
40. (Cancelled)

41. (Previously presented) The method of claim 26 wherein the composition additionally comprises one or more additional components selected from the group consisting of organic solvents and co-solvents, metal chelating or complexing agents, silicates, fluorides, additional metal corrosion inhibitors, surfactants, titanium residue removal enhancing agents, oxidizing agents and bath stabilizing agents.
42. (Cancelled)
43. (Previously presented) The method of claim comprising tetramethylammonium hydroxide, trans-(1,2-cyclohexylenedinitrilo)tetraacetic acid, hydrogen peroxide, water, and a metal halide compound selected from the group consisting of dihydrogen hexafluorosilicate, dihydrogenhexafluorogermanate, and ammonium hexafluorogermanate.
44. (Previously presented) The composition of claim 43 wherein the composition has a pH of about 11.5.
45. (Cancelled)
46. (Cancelled)
47. (Cancelled)
48. (Cancelled)